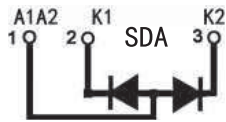
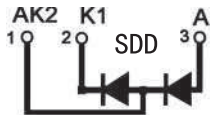


SDD/SDA/SDK100NXXB

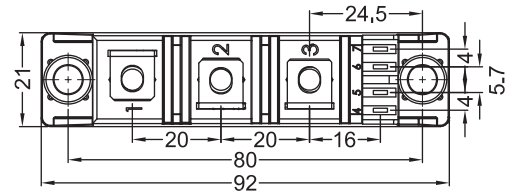
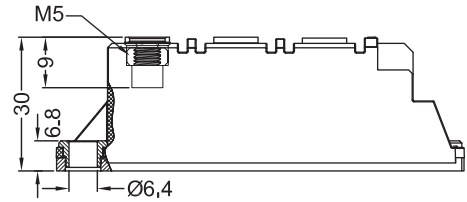
Diode-Diode Modules

□olerance:±0.5mm

Dimensions in mm (1mm=0.0394")



Type	V _{RSM} V	V _{RRM} V
SDD100N08B	900	800
SDD100N12B	1300	1200
SDD100N14B	1500	1400
SDD100N16B	1700	1600
SDD100N18B	1900	1800



Symbol	Test Conditions	Maximum Ratings	Unit
I _{FRMS} I _{FAVM}	T _{VJ} =T _{VJM} T _C =100°C; 180° sine	180 100	A
I _{FSM}	T _{VJ} =45°C V _R =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine	1700 1950	A
	T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	1540 1800	
∫ _i ² dt	T _{VJ} =45°C V _R =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine	14450 15700	A ² s
	T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	11850 13400	
T _{VJ} T _{VJM} T _{stg}		-40...+150 150 -40...+125	°C
V _{ISOL}	50/60Hz, RMS I _{ISOL} ≤1mA t=1min t=1s	3000 3600	V~
M _d	Mounting torque (M5) Terminal connection torque (M5)	2.5-4/22-35 2.5-4/22-35	Nm/lb.in.
Weight	Typ.	105	g

SDD/SDA/SDK100NXXB

Diode-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_R	T _{VJ} =T _{VJM} ; V _R =V _{RRM}	15	mA
V_F	I _F =300A; T _{VJ} =25°C	1.5	V
V_{TO}	For power-loss calculations only	0.8	V
r_T	T _{VJ} =T _{VJM}	2.3	mΩ
Q_S	T _{VJ} =125°C; I _F =50A; -di/dt=3A/us	170	uC
I_{RM}		45	A
R_{thJC}	per diode; DC current per module	0.35 0.175	K/W
R_{thJK}	per diode; DC current per module	0.55 0.275	K/W
d_s	Creepage distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.310749
- * RoHs compliant

APPLICATIONS

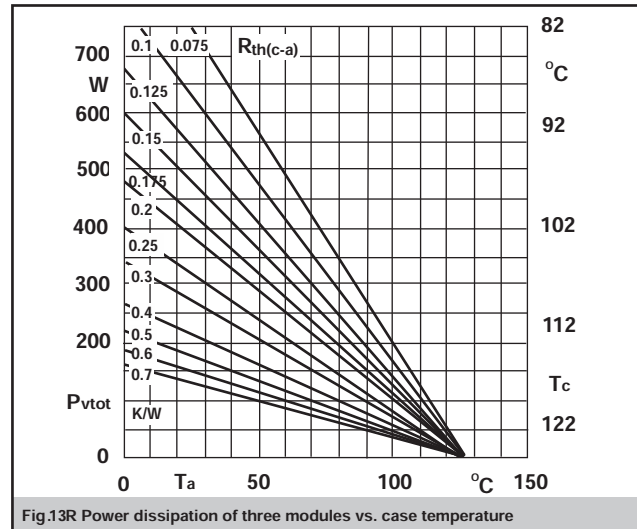
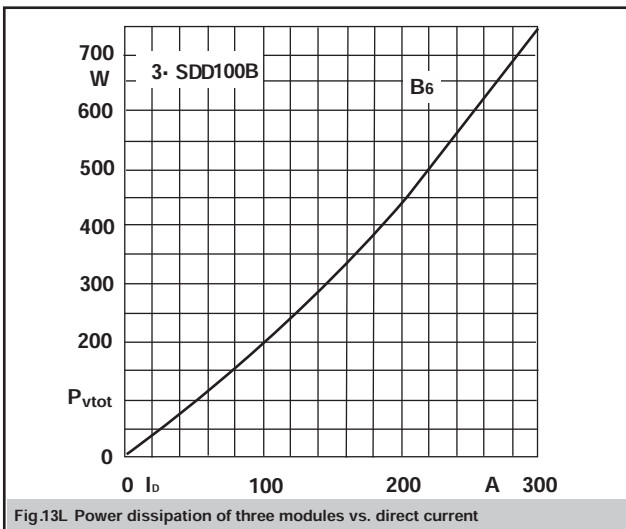
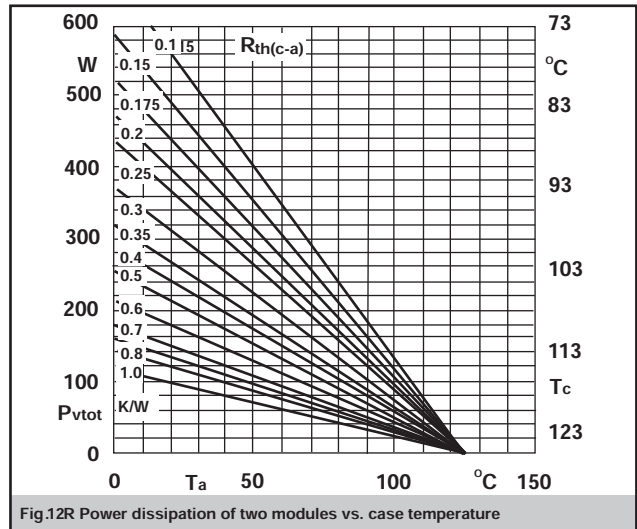
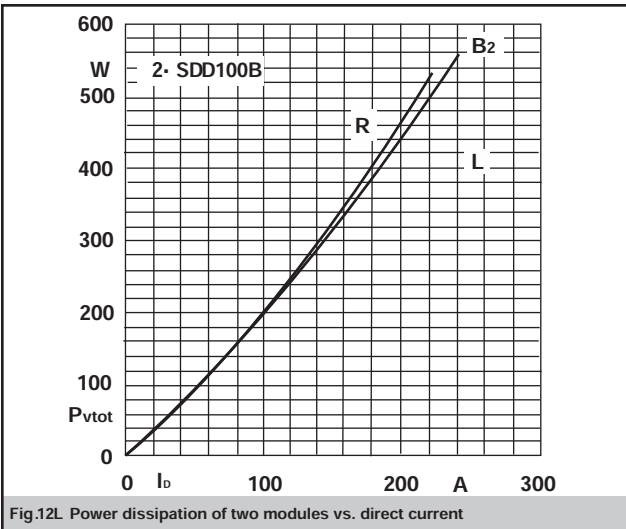
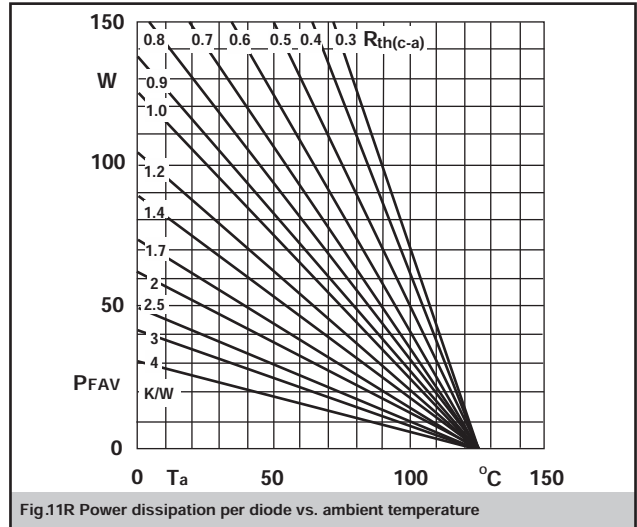
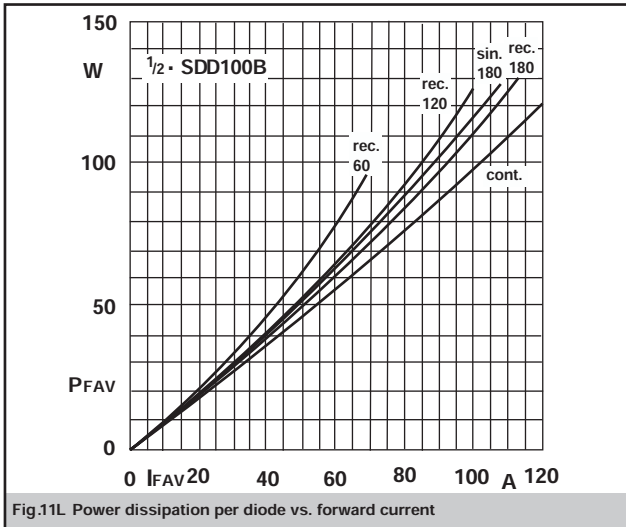
- * Supplies for DC power equipment
- * DC supply for PWM inverter
- * Field supply for DC motors
- * Battery DC power supplies

ADVANTAGES

- * Space and weight savings
- * Simple mounting
- * Improved temperature and power cycling
- * Reduced protection circuits

SDD/SDA/SDK100NXXB

Diode-Diode Modules



SDD/SDA/SDK100NXXB

Diode-Diode Modules

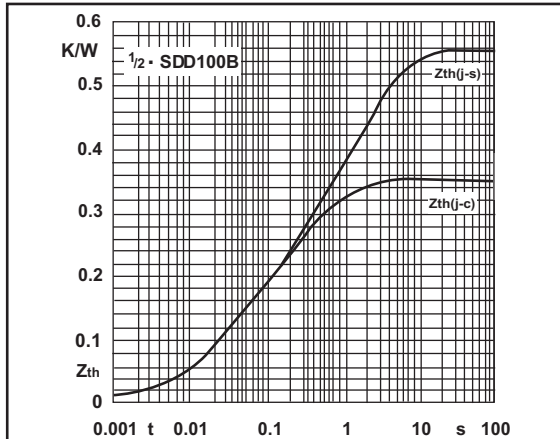


Fig.14 Transient thermal impedance vs. time

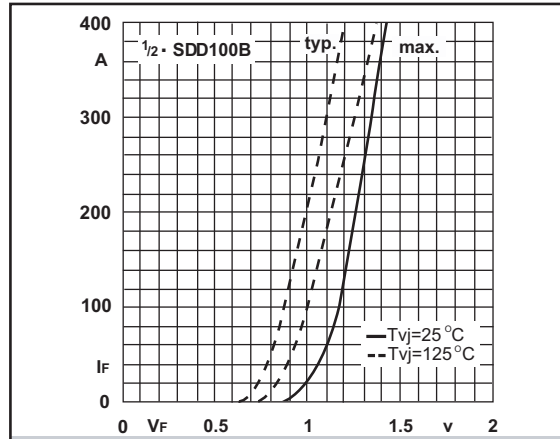


Fig.15 Forward characteristics

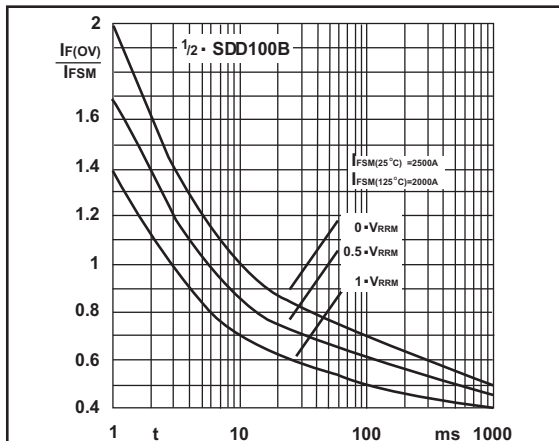


Fig.16 Surge overload current vs. time

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[T483C](#) [T484C](#) [T485F](#) [T485H](#) [T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#)
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[25.522.3353.0](#)